

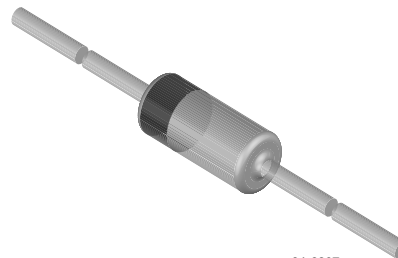
## Fast Switching Diode

### Features

- Silicon Epitaxial Planar Diode
- Low forward voltage drop
- High forward current capability

### Applications

High speed switch and general purpose use in computer and industrial applications



94 9367

### Mechanical Data

**Case:** DO-35 Glass Case

**Weight:** approx. 125 mg

**Packaging Codes/Options:**

TR / 10 k per 13 " reel (52 mm tape), 50 k/box

TAP / 10 k per Ammopack (52 mm tape), 50 k/box

### Parts Table

Part	Type differentiation	Ordering code	Remarks
1N4150	Single Diodes	1N4150-TR or 1N4150-TAP	Tape and Reel / Ammopack

### Absolute Maximum Ratings

$T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Repetitive peak reverse voltage		$V_{RRM}$	50	V
Reverse voltage		$V_R$	50	V
Peak forward surge current	$t_p = 1 \mu\text{s}$	$I_{FSM}$	4	A
Average peak forward current		$I_{FRM}$	600	mA
Forward current	$V_R = 0$	$I_F$	300	mA
Average forward current	$V_R = 0$	$I_{FAV}$	150	mA
Power dissipation	$l = 4 \text{ mm}, T_L = 45^{\circ}\text{C}$	$P_V$	440	mW
	$l = 4 \text{ mm}, T_L \leq 25^{\circ}\text{C}$	$P_V$	500	mW

### Thermal Characteristics

$T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Junction ambient	$l = 4 \text{ mm}, T_L = \text{constant}$	$R_{thJA}$	350	K/W
Junction temperature		$T_j$	175	$^{\circ}\text{C}$
Storage temperature range		$T_{stg}$	- 65 to + 175	$^{\circ}\text{C}$

## Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward voltage	$I_F = 1\text{ mA}$	$V_F$	0.54		0.62	V
	$I_F = 10\text{ mA}$	$V_F$	0.66		0.74	V
	$I_F = 50\text{ mA}$	$V_F$	0.76		0.86	V
	$I_F = 100\text{ mA}$	$V_F$	0.82		0.92	V
	$I_F = 200\text{ mA}$	$V_F$	0.87		1.0	V
Reverse current	$V_R = 50\text{ V}$	$I_R$			100	nA
	$V_R = 50\text{ V}, T_j = 150\text{ }^{\circ}\text{C}$	$I_R$			100	$\mu\text{A}$
Diode capacitance	$V_R = 0, f = 1\text{ MHz}, V_{HF} = 50\text{ mV}$	$C_D$			2.5	pF
Reverse recovery time	$I_F = I_R = (10\text{ to }100)\text{ mA}, i_R = 0.1 \times I_R, R_L = 100\text{ }\Omega$	$t_{rr}$			4	ns

## Typical Characteristics ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

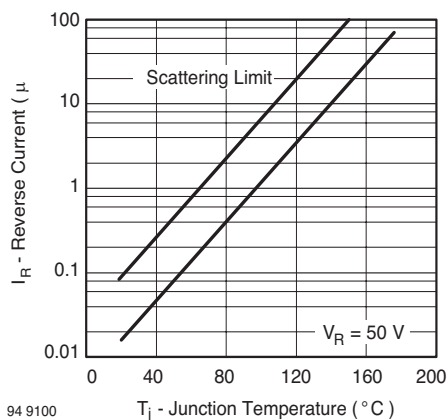


Fig. 1 Reverse Current vs. Junction Temperature

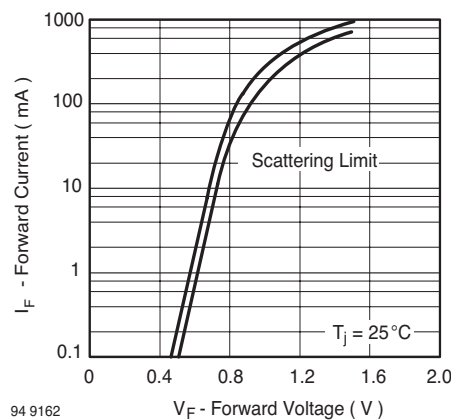
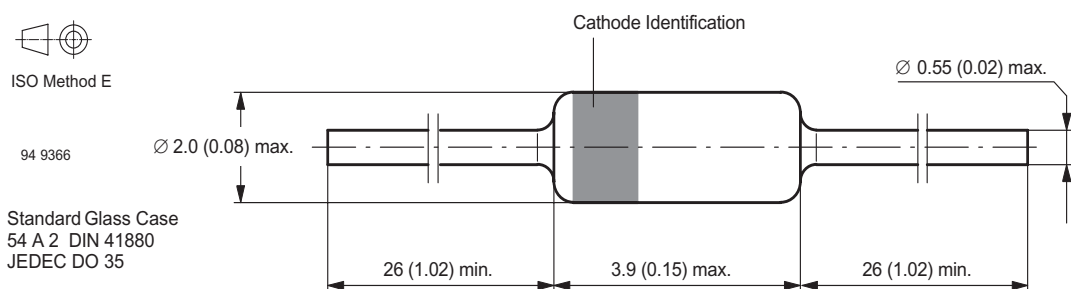


Fig. 2 Forward Current vs. Forward Voltage

## Package Dimensions in mm (Inches)



## **Ozone Depleting Substances Policy Statement**

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

**Vishay Semiconductor GmbH** has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

**Vishay Semiconductor GmbH** can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

### **We reserve the right to make changes to improve technical design and may do so without further notice.**

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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